1. General description

SiliconMAX standard level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product is designed and qualified for use in computing, communications, consumer and industrial applications only.

2. Features and benefits

- · Higher operating power due to low thermal resistance
- Low conduction losses due to low on-state resistance
- Suitable for high frequency applications due to fast switching characteristics

3. Applications

- DC-to-DC converters
- Switched-mode power supplies

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit		
V_{DS}	drain-source voltage	25 °C ≤ T _j ≤ 175 °C		-	-	200	V		
I _D	drain current	T _{mb} = 100 °C		-	-	27.5	А		
P _{tot}	total power dissipation	T _{mb} = 25 °C		-	-	250	W		
Static characte	ristics								
R _{DSon}	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 17 \text{ A}; T_j = 175 ^{\circ}\text{C}$		-	-	165	mΩ		
Dynamic chara	Dynamic characteristics								
Q_{GD}	gate-drain charge	$I_D = 39 \text{ A; } V_{DS} = 160 \text{ V; } V_{GS} = 10 \text{ V; } $ $T_j = 25 \text{ °C}$		-	37	50	nC		



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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	mb	
2	D	drain		
3	S	source		D
mb	D	mounting base; connected to drain	TO-220AB (SOT78)	mbb076 S

6. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
PSMN057-200P	TO-220AB	plastic, single-ended package (heatsink mounted, 1 mounting hole); 3 leads; 2.54 mm pitch; 15.6 mm x 10 mm x 4.4 mm body	SOT78			

7. Marking

Table 4. Marking codes

Type number	Marking code
PSMN057-200P	PSMN057 200P

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{DS}	drain-source voltage	25 °C ≤ T _j ≤ 175 °C	-	200	V
V_{DGR}	drain-gate voltage	25 °C ≤ Tj ≤ 175 °C; RGS = 20 kΩ	-	200	V
V_{GS}	gate-source voltage		-20	20	V
P _{tot}	total power dissipation	T _{mb} = 25 °C	-	250	W
I _D	drain current	T _{mb} = 100 °C	-	27.5	A
		T _{mb} = 25 °C	-	39	A
I _{DM}	peak drain current	pulsed; T _{mb} = 25 °C	-	156	A
T _{stg}	storage temperature		-55	175	°C
T _j	junction temperature		-55	175	°C
Source-drain di	ode				
Is	source current	T _{mb} = 25 °C	-	39	А

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Symbol	Parameter	Conditions		Min	Max	Unit
I _{SM}	peak source current	pulsed; T _{mb} = 25 °C		-	156	Α
Avalanche ruggedness						
E _{DS(AL)S}	source avalanche energy	I_D = 23 A; $V_{sup} \le 50$ V; R_{GS} = 50 Ω; V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; unclamped; t_p = 240 μs		-	925	mJ
I _{AS}	non-repetitive avalanche current	$V_{sup} \le 50 \text{ V}; V_{GS} = 10 \text{ V}; T_{j(init)} = 25 \text{ °C};$ $R_{GS} = 50 \Omega; \text{ unclamped}$		-	23	А

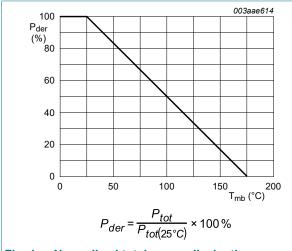


Fig. 1. Normalized total power dissipation as a function of mounting base temperature

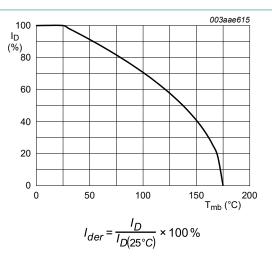


Fig. 2. Normalized continuous drain current as a function of mounting base temperature

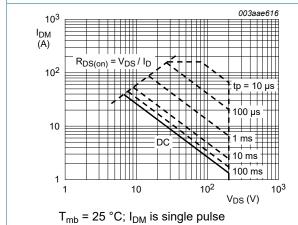
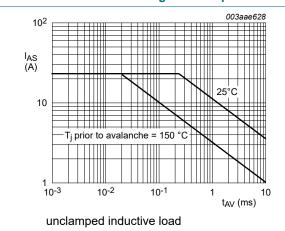


Fig. 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage



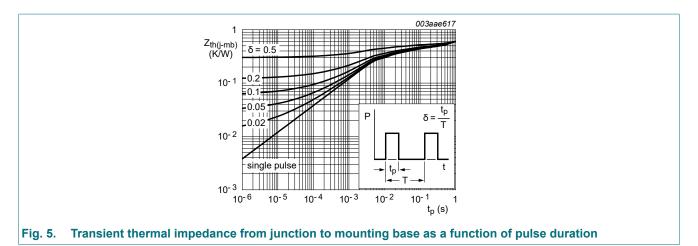
ig. 4. Single-shot avalanche rating; avalanche current as a function of avalanche period

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base		-	-	0.6	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	-	60	-	K/W

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10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
V _{(BR)DSS}	drain-source	I _D = 0.25 mA; V _{GS} = 0 V; T _j = -55 °C	178	-	-	V
	breakdown voltage	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	200	-	-	V
V _{GS(th)}	gate-source threshold	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C}$	-	-	6	V
	voltage	I _D = 1 mA; V _{DS} =V _{GS} ; T _j = 175 °C	1	-	-	V
		I _D = 1 mA; V _{DS} =V _{GS} ; T _j = 25 °C	2	3	4	V
I _{DSS}	drain leakage current	V _{DS} = 200 V; V _{GS} = 0 V; T _j = 25 °C	-	0.03	10	μΑ
		V _{DS} = 200 V; V _{GS} = 0 V; T _j = 175 °C	-	-	500	μΑ
I _{GSS}	gate leakage current	V _{GS} = 10 V; V _{DS} = 0 V; T _j = 25 °C	-	2	100	nA
		$V_{GS} = -10 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	2	100	nA
R _{DSon}	drain-source on-state	V _{GS} = 10 V; I _D = 17 A; T _j = 175 °C	-	-	165	mΩ
	resistance	V _{GS} = 10 V; I _D = 17 A; T _j = 25 °C	-	41	57	mΩ
Dynamic ch	naracteristics		'		'	
Q _{G(tot)}	total gate charge	I _D = 39 A; V _{DS} = 160 V; V _{GS} = 10 V;	-	96	-	nC
Q _{GS}	gate-source charge	T _j = 25 °C	-	13	-	nC
Q _{GD}	gate-drain charge		-	37	50	nC
C _{iss}	input capacitance	V _{DS} = 25 V; V _{GS} = 0 V; f = 1 MHz;	-	3750	-	pF
C _{oss}	output capacitance	T _j = 25 °C	-	385	-	pF
C _{rss}	reverse transfer capacitance		-	180	-	pF
t _{d(on)}	turn-on delay time	$V_{DS} = 100 \text{ V}; R_L = 2.7 \Omega; V_{GS} = 10 \text{ V};$	-	18	-	ns
t _r	rise time	$R_{G(ext)} = 5.6 \Omega; T_j = 25 ^{\circ}C$	-	58	-	ns
t _{d(off)}	turn-off delay time		-	105	-	ns
t _f	fall time		-	78	-	ns
L _D	internal drain inductance	measured from drain lead to centre of die; $T_j = 25$ °C	-	4.5	-	nH
		measured from tab to centre of die; $T_j = 25 ^{\circ}\text{C}$	-	3.5	-	nH
L _S	internal source inductance	measured from source lead to source bond pad; T _i = 25 °C	-	7.5	-	nΗ

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Symbol	Parameter	Conditions		Min	Тур	Max	Unit	
Source-drain diode								
V_{SD}	source-drain voltage	I _S = 25 A; V _{GS} = 0 V; T _j = 25 °C		-	0.85	1.2	V	
t _{rr}	reverse recovery time	$I_S = 20 \text{ A}$; $dI_S/dt = -100 \text{ A/}\mu\text{s}$; $V_{GS} = 0 \text{ V}$;		-	133	-	ns	
Q _r	recovered charge	$V_{DS} = 30 \text{ V}; T_j = 25 \text{ °C}$		-	895	-	nC	

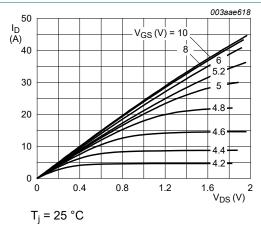


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

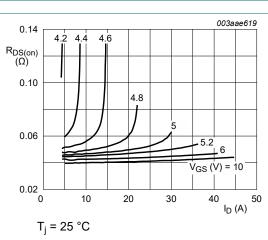


Fig. 7. Drain-source on-state resistance as a function of drain current; typical values

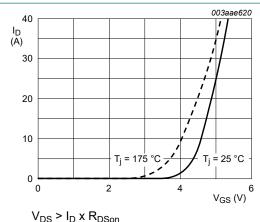


Fig. 8. Transfer characteristics: drain current as a function of gate-source voltage; typical values

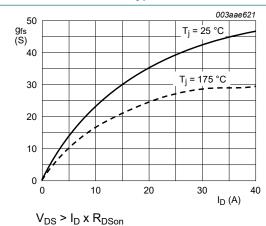


Fig. 9. Forward transconductance as a function of drain current; typical values

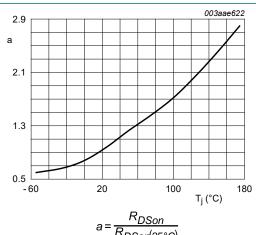


Fig. 10. Normalized drain-source on-state resistance factor as a function of junction temperature

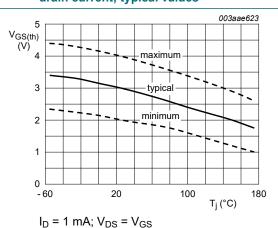


Fig. 11. Gate-source threshold voltage as a function of junction temperature

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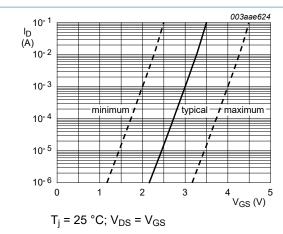


Fig. 12. Sub-threshold drain current as a function of gate-source voltage

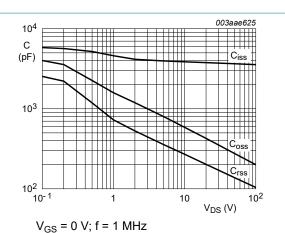


Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical

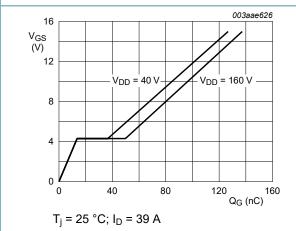


Fig. 14. Gate-source voltage as a function of gate charge; typical values

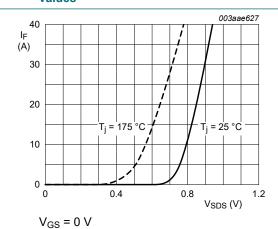
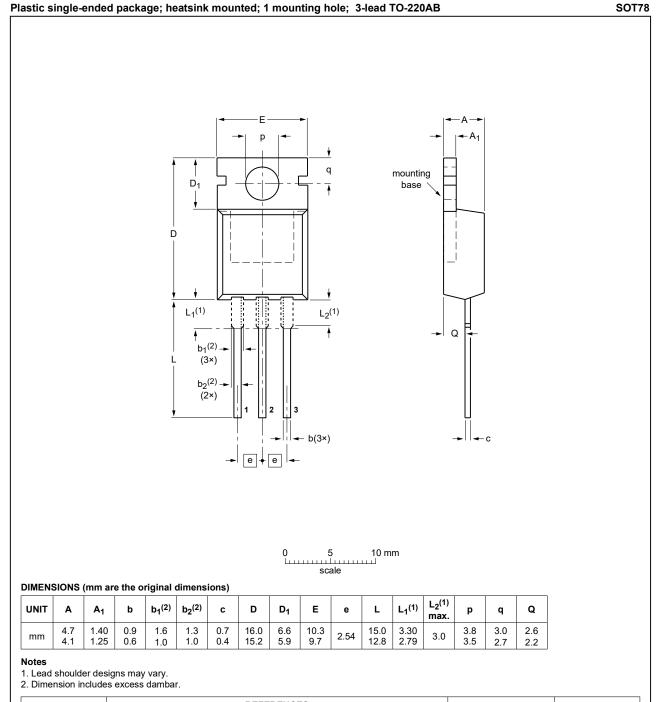


Fig. 15. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values

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11. Package outline



OUTLINE		REFERENCES			EUROPEAN	ISSUE DATE
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE
SOT78		3-lead TO-220AB	SC-46			08-04-23 08-06-13

Fig. 16. Package outline TO-220AB (SOT78)

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Document status [1][2]	Product status [3]	Definition		
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.		
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Product [short] data sheet	Production	This document contains the product specification.		

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